AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

1. (withdrawn) A semiconductor device comprising:

a gate dielectric film formed on a semiconductor substrate;

a gate electrode including:

a first electrode layer formed on the gate dielectric film;

a dielectric film having a thickness of 5 Å or more and 100 Å or less, and formed on the first electrode layer; and

a second electrode layer formed on the dielectric film; and

a source and drain regions formed in the semiconductor substrate at both sides of the gate electrode.

2-7. (cancelled)

8. (Currently Amended) A method of manufacturing a semiconductor device comprising:

forming a ~~gate~~ first dielectric film on a semiconductor substrate;

forming a first electrode material layer on the ~~gate~~ first dielectric film;

forming a second dielectric film having a thickness of 5 Å or more and 100 Å or less on the first electrode material layer;

forming a second electrode material layer on the second dielectric film;

forming a pattern on the second electrode material layer;

etching the second electrode material layer using the pattern as a mask, thereby exposing the second dielectric film;

etching the second dielectric film; and

etching the first electrode material layer, thereby forming a gate electrode.

9. (Original) The method of manufacturing a semiconductor device according to claim 8, wherein the second electrode material layer is formed of polycrystalline silicon or silicon germanium, to which an impurity is doped.

10. (Currently Amended) The method of manufacturing a semiconductor device according to claim 8, wherein the etching of the second electrode material layer to expose the second dielectric film is performed by using HBr gas or a mixed gas containing HBr gas and O_2 gas as an etching gas.

11. (Currently Amended) The method of manufacturing a semiconductor device according to claim 8, wherein the etching of the second electrode material layer includes:

etching the second electrode material layer using a first etching gas, and stopping etching before the second dielectric film is exposed; and

etching the second electrode material layer using a second etching gas until the second dielectric film is exposed.

12. (Original) The method of manufacturing a semiconductor device according to claim 11, wherein the first etching gas is one selected from the group consisting of HBr gas, a mixed gas containing HBr gas and Cl_2 gas, a mixed gas containing HBr gas, N_2 gas, and CF_4 gas, a mixed gas containing HBr gas, N_2 gas, and NF_3 gas, and a mixed gas containing HBr gas, N_2 gas, and CHF_3 gas.

13. (Original) The method of manufacturing a semiconductor device according to claim 11, wherein the second etching gas is one selected from the group consisting of HBr gas, a mixed gas containing HBr gas and O_2 gas, and a mixed gas containing HBr gas, Cl_2 gas, and O_2 gas.

14. (Currently Amended) The method of manufacturing a semiconductor device according to claim 8, wherein the second dielectric film is selected from the group consisting of a silicon oxide layer, a silicon nitride layer, a silicon oxynitride layer, and a

combined layer formed by laminating at least two of a silicon oxide layer, a silicon nitride layer, and a silicon oxynitride layer.

15. (Currently Amended) The method of manufacturing a semiconductor device according to claim 14, wherein a third etching gas used to etch the second dielectric film is one selected from the group consisting of CF_4 gas, SF_6 gas, NF_3 gas, and CHF_3 gas.

16. (Original) The method of manufacturing a semiconductor device according to claim 8, wherein the first electrode material layer is formed of polycrystalline silicon or silicon germanium, to which an impurity is doped.

17. (Currently Amended) The method of manufacturing a semiconductor device according to claim 8, wherein the etching of the first electrode material layer includes:

etching the first electrode material layer using a fourth etching gas until the ~~gate~~ first dielectric film is exposed; and

removing a residue of the first electrode material layer using a fifth etching gas.

18. (Original) The method of manufacturing a semiconductor device according to claim 17, wherein the fourth etching gas is one selected from the group consisting of HBr gas, a mixed gas containing HBr gas and O_2 gas, and a mixed gas containing HBr gas, Cl_2 gas, and O_2 gas.

19. (Original) The method of manufacturing a semiconductor device according to claim 17, wherein the fifth etching gas is one selected from the group consisting of a mixed gas containing HBr gas and O_2 gas, a mixed gas containing HBr gas, O_2 gas, and N_2 gas, and a mixed gas containing HBr gas, Cl_2 gas, and O_2 gas.

20. (Original) The method of manufacturing a semiconductor device according to claim 8, further comprising removing a natural oxide layer formed on a surface of the second electrode material layer before the etching of the second electrode material layer.

21. (Currently Amended) The method of manufacturing a semiconductor device according to claim 8, wherein the second dielectric film is formed ~~so as to~~ in contact with an upper surface of the first electrode material layer and the second electrode material layer is formed ~~so as to~~ in contact with an upper surface of the second dielectric film.

22. (Previously Presented) The method of manufacturing a semiconductor device according to claim 8, wherein a distance between an upper surface of the first electrode material layer and a lower surface of the second electrode material layer is 5Å to 100 Å.

23. (New) A method of manufacturing a semiconductor device comprising:

forming a first dielectric film on each of first and second regions in a semiconductor substrate;

forming first and second stack films on the first dielectric film of the first and second regions respectively, each of the first and second stack films having a first electrode material layer, a second dielectric film having a thickness of 5 Å or more and 100 Å or less, and a second electrode material layer, an etching rate of the first and second electrode material layers of the first stack film being different from an etching rate of the first and second electrode material layers of the second stack film;

forming a pattern on the first and second stack films;

etching the second electrode material layer of each of the first and second stack films using the pattern as a mask, thereby exposing the second dielectric film of each of the first and second stack films;

etching the second dielectric film of each of the first and second stack films; and

etching the first electrode material layer of each of the first and second stack films, thereby forming a gate electrode in each of the first and second regions.

24. (New) A method of manufacturing a semiconductor device according to claim 23, wherein the first and second electrode material layers of the first stack film are formed of polycrystalline silicon or silicon germanium, the first and second electrode material layers of the first stack film being doped with a first impurity, and the first and second electrode material layers of the second stack film are formed of polycrystalline

silicon or silicon germanium, the first and second electrode material layers of the second stack film being doped with a second impurity.